**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- · Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- · Sensitive gate for easy logic level triggering
- Triggering in all four quadrants

## 3. Applications

- · General purpose motor controls
- General purpose switching

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 110 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	4	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	35	А
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } \underline{Fig. 7}$	-	-	25	mA

**4Q Triac** 

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		N
3	G	gate		T2 — T1
mb	T2	mounting base; main terminal 2		sym051
			1 2 3	

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BTA234-800E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 110 °C; Fig. 1; Fig. 2; Fig. 3	-	4	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig 4; Fig 5	-	35	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	38.5	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	6.1	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA; T2+ G+	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 50 mA; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_GM$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

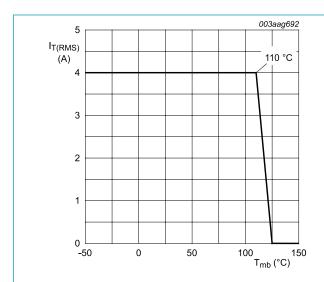
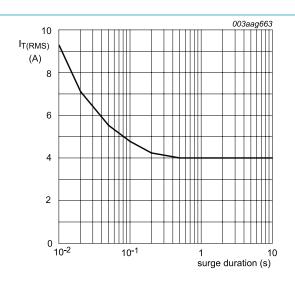


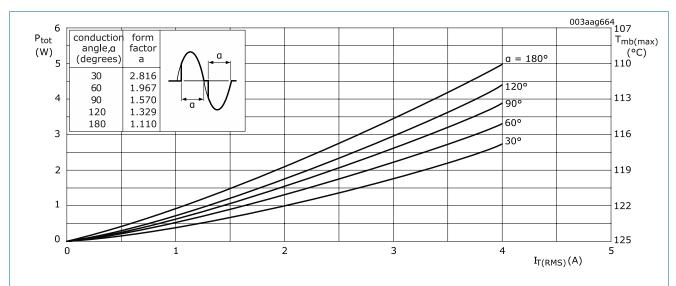
Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 110 \text{ }^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values

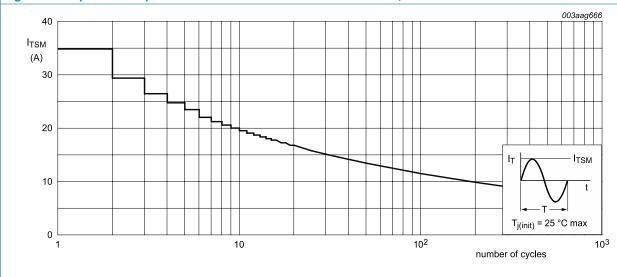
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 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

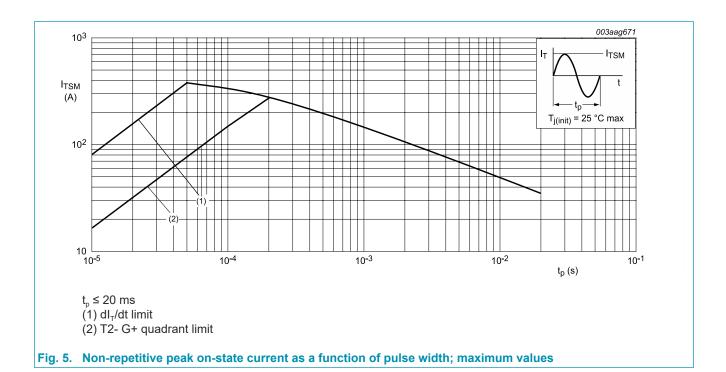
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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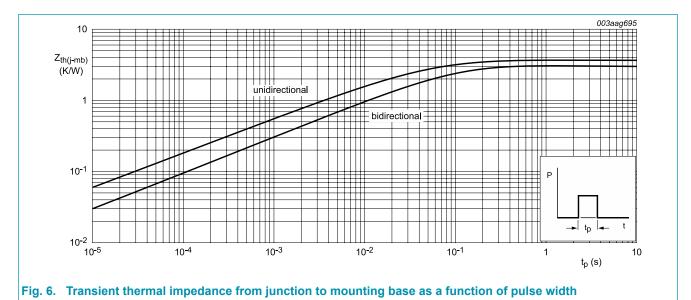


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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; Fig. 6	-	-	3.7	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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## 9. Characteristics

### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	gate trigger current $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$				
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	25	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	15	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A;T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	0.7	1	V
		V <sub>D</sub> = 400V; I <sub>T</sub> = 0.1 A;T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	80	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/$ dt = 1.8 A/ms; $I_T$ = 4 A; gate open circuit	15	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; Tj = 125 C; $I_{T(RMS)}$ = 4 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	15	-	-	A/ms
$\mathbf{t}_{gt}$	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

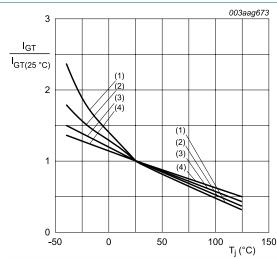
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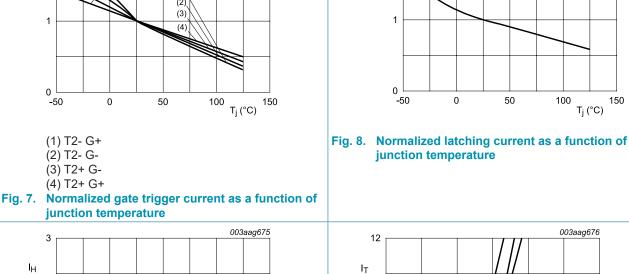
T<sub>i</sub> (°C)

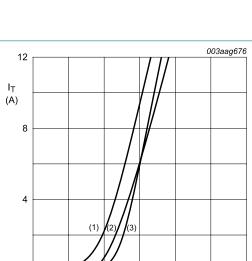
3

 $V_T(V)$ 

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3

2

1

n

-50

ΙL

T<sub>L(25°C)</sub>



50

0

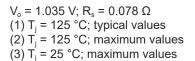


Fig. 10. On-state current as a function of on-state voltage

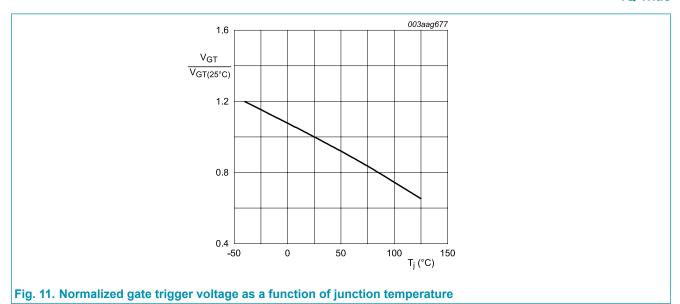
150

T<sub>H(25°C)</sub>

2

0 -50

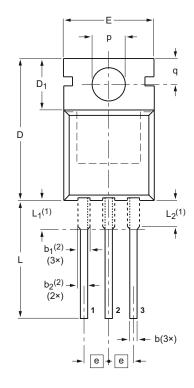
**4Q Triac** 

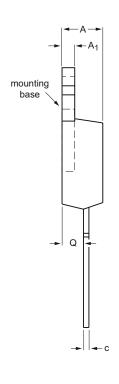


# 10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





0 5 10 mm

### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13	

**40 Triac** 

### 11. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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### 12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
	Ordering information	
	Limiting values	
	Thermal characteristics	
9.	Characteristics	7
10	. Package outline	10
	. Legal information	
	Contents	

For more information, please visit: http://www.ween-semi.com
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